

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A plasma processing system comprising:

a process chamber;

an upper electrode assembly;

a plurality of pressure detectors configured to detect pressures in a plurality of locations in the process chamber;

a chuck assembly including a support surface configured to support a wafer; and

a fluid flow control member including a plurality of recesses, said fluid flow control member located on the chuck assembly and surrounding the support surface of the chuck assembly, the fluid flow control member having an upper surface substantially in a same plane as the support surface of the chuck assembly when the fluid flow control member is in a withdrawn position. [[; and]]

wherein the [[a]] chuck assembly includes including a plurality of lift pin assemblies[[,]] for lifting the fluid flow control member at at least one location, each lift pin assembly including a lift pin configured to engage with a respective recess of the fluid flow control member to directly lift the fluid flow control member to an extended position such that the upper surface of the fluid flow control member extends above the support surface of the chuck assembly, the lift pins configured to be controlled based on the pressures detected by the plurality of pressure detectors.

Claim 2 (Original): The plasma processing system of claim 1 wherein the chuck assembly comprises at least one of an RF electrode and an electrostatic clamping electrode.

Claim 3 (Original): The plasma processing system of claim 1 wherein the fluid flow control member comprises a focus ring.

Claim 4 (Withdrawn): The plasma processing system of claim 1 wherein the fluid flow control member comprises a pumping baffle.

Claim 5 (Withdrawn): The plasma processing system of claim 1 wherein the fluid flow control member comprises an auxiliary focus ring.

Claim 6 (Original): The plasma processing system of claim 1 wherein lift pins of each of the plurality of lift pin assemblies are lifted simultaneously.

Claim 7 (Original): The plasma processing system of claim 1 wherein lift pins of each of the plurality of lift pin assemblies are controllable to be lifted individually.

Claim 8 (Canceled).

Claim 9 (Original): The plasma processing system of claim 1, further comprising a vacuum port located next to at least one of the plurality of lift pin assemblies.

Claims 10 and 11 (Canceled).

Claim 12 (Previously Presented): The plasma processing system of claim 1, wherein the lift pin extends through a horizontal surface of the chuck assembly when the lift pin is fully retracted.

Claim 13 (Previously Presented): The plasma processing system of claim 12, wherein the lift pin engages the respective recesses of the fluid flow control member when the lift pin is fully retracted.

Claim 14 (Currently Amended): A plasma processing system comprising:  
a process chamber;  
an upper electrode assembly;  
a plurality of pressure detectors configured to detect pressures in a plurality of locations in the process chamber;  
a chuck assembly including a support surface configured to support a wafer; and  
a fluid flow control member including a plurality of recesses, said fluid flow control member located on the chuck assembly and surrounding the support surface of the chuck assembly, the fluid flow control member having an upper surface substantially in a same plane as the support surface of the chuck assembly when the fluid flow control member is in a withdrawn position; and  
wherein the [[a]] chuck assembly includes including a plurality of lifting means for lifting the fluid flow control member at at least one location, each lifting means engaging a respective recess of the fluid flow control member to directly lift the fluid flow control member to an extended position such that the upper surface of the fluid flow control member extends above the support surface of the chuck assembly, the lifting means being controlled based on the pressures detected by the plurality of pressure detectors.

Claim 15 (Previously Presented): The plasma processing system of claim 14, wherein the lifting means extends through a horizontal surface of the chuck assembly when the lifting means is fully retracted.

Claim 16 (Previously Presented): The plasma processing system of claim 15, wherein the lifting means engages the respective recesses of the fluid flow control member when the lifting means is fully retracted.

Claim 17 (Previously Presented): The plasma processing system of claim 14 wherein the fluid flow control member comprises a focus ring.

Claim 18 (Withdrawn): The plasma processing system of claim 14 wherein the fluid flow control member comprises a pumping baffle.

Claim 19 (Withdrawn): The plasma processing system of claim 14 wherein the fluid flow control member comprises an auxiliary focus ring.

Claim 20 (Previously Presented): The plasma processing system of claim 14 wherein the plurality of lifting means are lifted simultaneously.

Claim 21 (Previously Presented): The plasma processing system of claim 14 wherein the plurality of lifting means are controllable to be lifted individually.

IN THE DRAWINGS

The attached sheet of drawings includes changes to Figure 4.

Attachment: One Replacement Sheet